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Spontaneous Spin-Polarization of Ballistic Electrons in Single Mode Quantum Wires due to Spin-Splitting

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We show that a quantum wire device with spin splitting can work as an active spin polarizer. Hot electrons in one 'spin' subband (e.g. 'spin-up') may pass such a device with weak electron pair scattering, while electrons in the opposite subband ('spin-down') may have high conversion probability into the 'spin-up' subband, resulting in spin polarization of a hot electron beam. Under different circumstances a hot electron beam passing through a single mode quantum wire may induce a steady state magnetization of the background electron gas in a section of the wire weakly coupled to the environment.

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In the present letter we predict two related new effects, achievable in devices based on single mode quantum wires with spin splitting of the electron bands: (1) a quantum wire structure, acting as an active spin polarizer for hot electrons, and (2) a device structure where a beam of hot electrons induces a steady state magnetization of the background electron gas in a section of the quantum wire. These effects allow the construction of several new devices and experiments. One possibility is the exploration of the spin resolved band structure and magnetic properties of quantum dots and other microstructures.

Transport in electron wave guides and in quantum wires is presently an active area of research (for a review see Ref. [1]). It is expected, that the transition from two-dimensional (2D) to single mode one-dimensional (1D) systems will show even more dramatic effects than the step from three dimensions (3D) to 2D. Two interesting effects are predicted here. We are here mainly concerned with transport in narrow single mode high mobility quantum wires (i.e. with a width around 10nm) and carriers with an excess energy (typically a few meV) above the Fermi energy, although we expect that the present results can be more generally applied.

Fig. 1 introduces electron pair scattering processes in 'single mode' quantum wires. This type of process breaks the electron phase. Although not flipping electron spin directly, it acts effectively like a spin flip process. The scattering partners must be in different 'spin' subbands | in a strictly 1D quantum wire, first order electron pair scattering is forbidden for partners in the same spin subband. (In 2D, for comparison, pair scattering for electrons in the same spin subband is not forbidden, but expected to be about 50% weaker than for pairs with partners in opposite spin subbands [2]).

The bands in bulk semiconductors lacking inversion symmetry are in general spin-split in zero magnetic field, with splitting term proportional to $\mathbf{k} \cdot \mathbf{j}$ and $\mathbf{k} \cdot \mathbf{j}^3$ [3]. In group III-V quantum wells or hetero-structures there are additional spin splitting terms due to microscopic electric fields and confinement [4] [5]. Spin splitting in 2D has recently been experimentally demonstrated by Raman scattering [6] and in transport [7] [8]. Fascinating new transport effects due to spin splitting have been predicted recently [9]. Splitting of the spin subbands

is also expected for quantum wires. In quantum wires, the wave functions of the two spin split subbands will have mixed character. We label 'spin-up' and 'spin-down' bands here according to the major contribution.

Fig. 2 (a) shows a typical electron-electron pair scattering process in a quantum wire with spin-splitting. An electron in the 'spin-up' subband at $(p_1; \uparrow)$ scatters with a spin-down electron at $(k_1; \downarrow)$, resulting in a hole at $(k_1; \downarrow)$, and electrons at $(k_1 - q_1; \downarrow)$ and at $(p_1 + q_1; \uparrow)$. This process has a much lower probability than a similar process for an electron in the 'spin-down' subband, because the final state $(p_1 + q_1; \uparrow)$ has a high probability of being occupied, while the state k_1 has a high probability of being empty. Therefore, an electron injected into the 'spin-up' subband is likely to pass the quantum wire without scattering. An electron $(k_2 - q_2; \downarrow)$ injected into the 'spin-down' subband, on the other hand, has an increased scattering probability as shown in Fig. 2 (b). There is a high probability that an injected electron in the 'spin-down' subband is converted into a hot 'spin-up' subband electron at similar energy. Therefore the quantum wire can act as an active electron polarizer. This effect relies on the k dependence of the spin splitting, mentioned above. The polarizer effect survives mixing of the spin subband wave functions due to confinement.

For our calculation we express the scattering rate for an electron at wavevector p with spin σ as:

$$\frac{1}{\tau_{ee, p; \sigma}} = \frac{2}{h} \sum_{k, q, \sigma'} f_{k; \sigma'} (1 - f_{k - q; \sigma'}) (1 - f_{p + q; \sigma}) \frac{\hbar k \cdot q; \sigma; p + q; \sigma' \cdot j \cdot k; \sigma; p; \sigma'}{(q; (E_{p; \sigma} - E_{p + q; \sigma'}) = \hbar) (E_{p + q; \sigma} + E_{k - q; \sigma'} - E_{p; \sigma} - E_{k; \sigma'})} \quad (1)$$

where $\hbar k \cdot q; \sigma; p + q; \sigma' \cdot j \cdot k; \sigma; p; \sigma' = e^2 F_{ijkl}^{1D}(q - w) = (L_0 r)$ is the 1D Coulomb interaction matrix element. $F_{ijkl}^{1D}(q - w)$ is the Coulomb Form factor, calculated by numerical integration, and w is the wire width. The dielectric function $(q; (E_{p; \sigma} - E_{p + q; \sigma'}) = \hbar)$ is calculated by integrating Ehrenreich's expression taking account of finite temperature and the spin-split electron band structure including non-parabolicity. The spin subband dependence of the electron pair scattering rates reported in this letter is caused by the Fermi population factor $f_{k; \sigma'} (1 - f_{k - q; \sigma'}) (1 - f_{p + q; \sigma})$.

Equation 1 is integrated numerically, taking a quantum wire of width $100\text{\AA}$ and square profile, with electron density $n = 1.6 \times 10^6 \text{ cm}^{-1}$ and at temperature $T = 1.4\text{K}$, and with infinite confinement potential. We include a single 'spin-up' band and a single 'spin-down' band. For the band dispersion we use that of bulk GaAs in the [110] orientation as a model. In an experimental quantum wire, the precise value of the spin-splitting and the composition of the wave functions will depend on the crystallographic details and the microscopic electric fields present in the structure. Spin splitting is expected to be around 1m eV in GaAs near the Fermi energy, thus limiting the predicted effects to temperatures below around 10K . Higher temperatures are possible for materials with stronger spin splitting. Fig. 3 shows, that the 'forward' pair scattering rate (i.e. with partners near $+k_F$) increases with increasing excess energy for one 'spin' subband (here 'spin down') while it remains suppressed for electrons in the opposite 'spin' subband (here 'spin-up'). The 'spin' subband dependence is almost absent for the weaker 'backward' scattering, i.e. with partners near $-k_F$. Calculations show that for hot electrons on balance a strong spin subband dependence of the total scattering rates remains.

Fig. 4 demonstrates schematically the construction of such a quantum wire spin polarizer. The wire length has to be less than the scattering length for 'spin-up' electrons (using the convention of the present Letter), less than the probability for scattering with partners near k_F and longer than the scattering rate for electrons in the 'spin-down' subband. Calculation shows that this can be fulfilled in GaAs-AlGaAs based quantum wires, for excess energies of the order of 5m eV , operating temperatures of $T = 4\text{K}$ or below, and wire lengths in the μm -range. Acoustic phonon scattering is expected to be weaker than electron scattering effects up to at least 100K , while we expect that optical phonon scattering will destroy this effect above approximately 100K . Sufficiently high mobility is required, so that impurity and roughness scattering are lower than electron-electron scattering. Since in-built microscopic electric fields affect the spin-splitting of the quantum wire, and since interface roughness can affect microscopic electric field, it could also negatively affect the

spin polarization phenomena. Plasmon scattering is a possible loss mechanism reducing efficiency and is neglected here.

So far we have assumed that the background electron gas in the wire is sufficiently coupled to the environment, so that its distribution is not disturbed by the injected electron beam. The opposite limit is the case of weak coupling of the background electrons in a section of the wire to the surroundings, as demonstrated in Fig. 5. In this case the injected electron beam will flip background electrons between spin subbands with unequal probability, leading to unequal spin populations and a steady state magnetization of the background electrons.

In summary, we have shown that an active electron spin polarizer can be constructed from a quantum wire with spin splitting of electron bands. We have calculated the spin dependent differential electron pair scattering rates as a function of electron excess energy. We have introduced a further related effect: a hot electron beam can induce spin polarization (corresponding to a steady state magnetization) in a section of a quantum wire, which is weakly coupled to the surroundings. This work opens the possibility of a large range of spin dependent experiments in microelectronic structures.

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REFERENCES

- [1] C . W . Beenakker and H . van Houten, *Solid State Physics*, ed. by H . Ehrenreich and D . Turnbull, Academic Press (San Diego) 44, 1 (1991).
- [2] G . Fasol and H . Sakaki, *Solid State Commun.* 84, 77 (1992).
- [3] M . Cardona, N . E . Christensen, and G . Fasol, *Phys. Rev. Lett.* 56, 2831 (1986), and *Phys. Rev. B* 38, 1806 (1988).
- [4] G . Lommer, F . Malcher, and U . Rossler, *Phys. Rev. Lett.* 60, 728 (1988).
- [5] G . Bastard, *Wave Mechanics Applied to Semiconductor Heterostructures*, Les Editions de Physiques, Les Ulis, (1990).
- [6] B . Jusserand, D . Richards, H . Peric, and B . Etienne, *Phys. Rev. Lett.* 69, 848 (1992).
- [7] B . Das, D . C . Miller, S . Datta, R . Reifengerger, W . P . Hong, P . K . Bhattacharya, J . Singh, and M . Jais, *Phys. Rev. B* 39 1411 (1989).
- [8] P . D . Dresselhaus, C . M . A . Papavassiliou, R . G . Wheeler, and R . N . Sacks, *Phys. Rev. Lett.* 68, 106 (1992).
- [9] G . Goldoni and A . Fasolino, *Phys. Rev. Lett.* 69, 2567 (1992).

FIGURES

FIG .1. Diagram of intrasubband electron-electron pair scattering processes in a quantum wire: the electron pair $(p; k)$ undergoes a pair scattering process, resulting in the pair $(p'; k')$. In a quantum wire only electron pairs with partners in different 'spin' subbands can scatter. These processes, introduced here, break the electron phase and have the character of spin flip processes.

FIG .2. This figure demonstrates that a stream of hot electrons injected into a single mode quantum wire with an excess energy above the Fermi level may become spin polarized. (a) A spin-up electron injected with excess energy and wave vector p_1 has low scattering probability. (b) An injected electron injected into the 'spin-down' subband with wave vector $k_2 = q_2$ has high scattering probability, represented by bold arrows. After such pair scattering, a hot electron with spin up at p_1 is produced, which has again low scattering probability. Thus for a stream of hot electrons, the component in the 'spin-down' subband may be converted into 'spin-up' subband electrons, while the 'spin-up' component may pass with little scattering.

FIG .3. Differential electron-electron pair scattering rates as a function of the wave vector of the scattering partner for the two spin orientations, and for different excess energy measured from the Fermi surface. For hot electrons ($\epsilon > 0$), electron pair scattering rates may be orders of magnitude larger for one of the two spin subbands (here spin-down) than for the opposite orientation. This effect is due to the Fermi population factors and the Pauli principle. (Divergences in the calculated scattering rates at the point $q = 0$ have been eliminated from the Figure. They are typical for 1D systems, are not expected to break electron phase, and are not important for hot electrons). Note that the scattering rates are only weakly spin subband dependent for 'backward' scattering, i.e. $q \approx 2k_F$. Calculations show that for hot electrons a strong spin subband dependence of the total scattering rates survives.

FIG .4. Schematic design of an active quantum wire spin polarizer. (a) Outline of the conduction band potential of the wire structure. (b) population of the lowest 'spin-up' conduction subband, (c) population the lowest 'spin-down' subband as a function of position in the wire.

FIG. 5. Schematic diagram showing induced partial spin polarization (corresponding to and induced steady state magnetization) expected for a hot electron beam propagating through a section of a quantum wire with spin split electron bands, in which the background electrons are weakly coupled to the background. Shaded areas indicates steady state distribution of passing hot electron beam, while the thick curves indicate the population of the background electrons in the quantum wire | note the unequal number of populated 'spin-up' and 'spin-down' bands representing an induced magnetization.